

# Power Transistor (−80V, −7A)

## 2SB1290

●Features

- 1) Low  $V_{CE(sat)}$ . (Typ. −0.3V at  $I_C/I_B = -4/-0.4A$ )
- 2) Excellent DC current gain characteristics.
- 3)  $P_c=30W$  ( $T_c=25^\circ C$ )
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SD1833.

●Packaging specifications and  $h_{FE}$

Type	2SB1290
Package	TO-220FP
$h_{FE}$	EF
Code	—
Basic ordering unit (pieces)	500

●Absolute maximum ratings ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CB0}$	−80	V
Collector-emitter voltage	$V_{CE0}$	−80	V
Emitter-base voltage	$V_{EB0}$	−5	V
Collector current	$I_C$	−7	A (DC)
		−10	A (Pulse) *
Collector power dissipation	$P_c$	2	W
		30	W ( $T_c=25^\circ C$ )
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature	$T_{stg}$	−55~150	$^\circ C$

\* Single pulse  $P_w=100ms$

●Electrical characteristics ( $T_a=25^\circ C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CB0}$	−80	—	—	V	$I_C = -50 \mu A$
Collector-emitter breakdown voltage	$BV_{CE0}$	−80	—	—	V	$I_C = -1mA$
Emitter-base breakdown voltage	$BV_{EB0}$	−5	—	—	V	$I_E = -60 \mu A$
Collector cutoff current	$I_{CBO}$	—	—	−10	$\mu A$	$V_{CB} = -80V$
Emitter cutoff current	$I_{EBO}$	—	—	−10	$\mu A$	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	−1	V	$I_C/I_B = -4A/-0.4A$ *
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	−1.5	V	$I_C/I_B = -4A/-0.4A$ *
DC current transfer ratio	$h_{FE}$	100	—	320	—	$V_{CE}/I_C = -5V/-1A$
Transition frequency	$f_T$	—	12	—	MHz	$V_{CE} = -5V, I_E = 0.5A, f = 5MHz$
Output capacitance	$C_{ob}$	—	200	—	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$

\* Measured using pulse current

(96-630-B55)

# Power Transistor (80V, 7A)

## 2SD1833

●Features

- 1) Low  $V_{CE(sat)}$ . (Typ. 0.3V at  $I_C/I_B = 4/0.4A$ )
- 2) Excellent DC current gain characteristics.
- 3)  $P_c=30W$  ( $T_c=25^\circ C$ )
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SB1290.

●Packaging specifications and  $h_{FE}$

Type	2SD1833
Package	TO-220FP
$h_{FE}$	DEF
Code	—
Basic ordering unit (pieces)	500

●Absolute maximum ratings ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CB0}$	100	V
Collector-emitter voltage	$V_{CE0}$	80	V
Emitter-base voltage	$V_{EB0}$	5	V
Collector current	$I_C$	7	A (DC)
		10	A (Pulse) *
Collector power dissipation	$P_c$	2	W
		30	W ( $T_c=25^\circ C$ )
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature	$T_{stg}$	−55~150	$^\circ C$

\* Single pulse  $P_w=100ms$

●Electrical characteristics ( $T_a=25^\circ C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CB0}$	100	—	—	V	$I_C = 50 \mu A$
Collector-emitter breakdown voltage	$BV_{CE0}$	80	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	$BV_{EB0}$	5	—	—	V	$I_E = 60 \mu A$
Collector cutoff current	$I_{CBO}$	—	—	10	$\mu A$	$V_{CB} = 100V$
Emitter cutoff current	$I_{EBO}$	—	—	10	$\mu A$	$V_{EB} = 4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	1	V	$I_C/I_B = 4A/0.4A$ *
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C/I_B = 4A/0.4A$ *
DC current transfer ratio	$h_{FE}$	60	—	320	—	$V_{CE} = 5V, I_C = 1A$ *
Transition frequency	$f_T$	—	5	—	MHz	$V_{CE} = 5V, I_E = -0.5A, f = 5MHz$ *
Output capacitance	$C_{ob}$	—	150	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

\* Measured using pulse current

(96-741-D55)

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